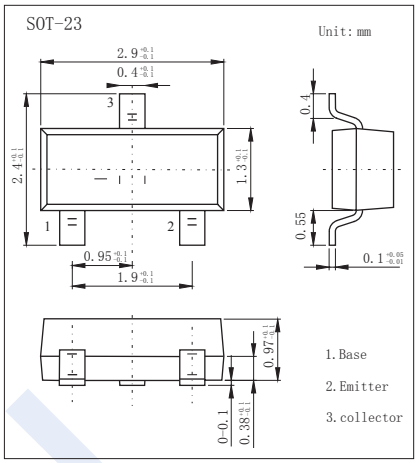
PNP Transistors

2SA1171



■ Features

● Low frequency small signal amplifier

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-90	V
Collector to emitter voltage	V_{CEO}	-90	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA， I_E=0	-90			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA，R_{BE}=∞	-90			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A， I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -75 V , I_E=0			-0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA			-1.2	
Base-emitter voltage	V_{BE}	V_{CE}=-12V,I_C=-2mA			-0.75	
DC current transfer ratio	h_{FE}	V_{CE}=-12V,I_C=-2mA	250		800	
Collector output capacitance	C_{ob}	V_{CB}= -25 V , I_E=0, f=1MHz		1.6		pF
Transition frequency	f_T	V_{CE}=-12V, I_C=-2 mA		200		MHz

■ Classification of hfe

Marking	PD	PE
hFE	250～500	400～800

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■ Typical Characterisitics